



## General Description

This product family offers state of the art performance. It is designed for high frequency applications where high efficiency and high reliability are required.



SMBF

## Features

- Low conduction loss due to low  $V_F$
- Extremely low switching loss by tiny  $Q_C$
- Highly rugged due to better surge current
- Industrial standard quality and reliability

## Applications

- UPS
- Power Inverter
- High performance SMPS
- Power factor correction



Part Number	Package	Brand
H1D04065 BF	SMBF	HXY MOSFET

## Maximum Ratings ( $T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
$V_{RRM}$	Repetitive Peak Reverse Voltage	650	V	
$V_{RSM}$	Surge Peak Reverse Voltage	650	V	
$V_R$	DC Peak Reverse Voltage	650	V	
$I_F$	Continuous Forward Current	8 4.5 4	A	$T_C=25^{\circ}\text{C}$ $T_C=135^{\circ}\text{C}$ $T_C=145^{\circ}\text{C}$
$I_{FRM}$	Repetitive Peak Forward Surge Current	23 15	A	$T_C=25^{\circ}\text{C}$ , $t_p=10$ ms, Half Sine Pulse $T_C=110^{\circ}\text{C}$ , $t_p=10$ ms, Half Sine Pulse
$I_{FSM}$	Non-Repetitive Forward Surge Current	36 28	A	$T_C=25^{\circ}\text{C}$ , $t_p=10$ ms, Half Sine Pulse $T_C=110^{\circ}\text{C}$ , $t_p=10$ ms, Half Sine Pulse
$P_{tot}$	Power Dissipation	28 11	W	$T_C=25^{\circ}\text{C}$ $T=110^{\circ}\text{C}$
$\int i^2 dt$	$i^2 t$ value	6.5 3.9	$\text{A}^2\text{s}$	$T_C=25^{\circ}\text{C}$ , $t_p=10$ ms $T_C=110^{\circ}\text{C}$ , $t_p=10$ ms
$T_J$	Operating Junction Range	-55 to +175	$^{\circ}\text{C}$	
$T_{slg}$	Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$	



## Electrical Characteristics

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Forward Voltage	$V_F$	-	1.3	1.5	V	$I_F = 4A$ $T_J = 25^{\circ}C$ $T_J = 175^{\circ}C$
Reverse Current	$I_R$	-	10	50	$\mu A$	$V_R = 650V$ $T_J = 25^{\circ}C$ $T_J = 175^{\circ}C$
Total Capacitive Charge	$Q_C$	-	10.6	-	nC	$V_R = 400V, T_J = 25^{\circ}C$ $Q_C = \int_0^{V_R} C(V) dV$
Total Capacitance	C	-	203	-	pF	$T_J = 25^{\circ}C, f = 1MHz$ $V_R = 0V$ $V_R = 200V$ $V_R = 400V$

## Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	Thermal Resistance from Junction to Case	6.0	$^{\circ}C/W$

## Characteristics Curve

Fig 1: Forward Characteristics

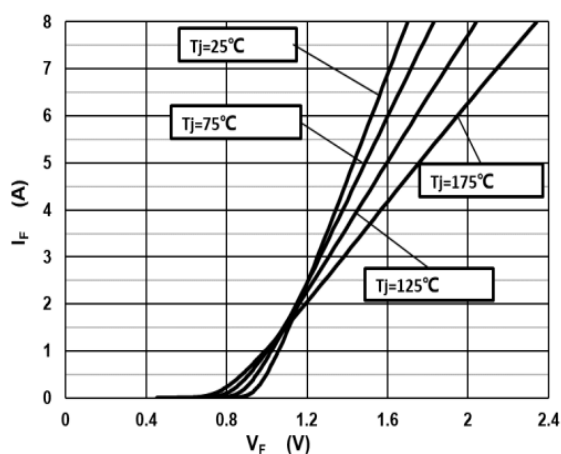


Fig 2: Reverse Characteristics

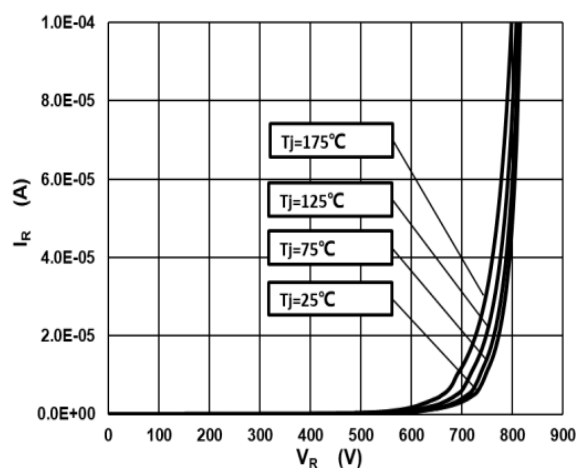




Fig 3: Current Derating

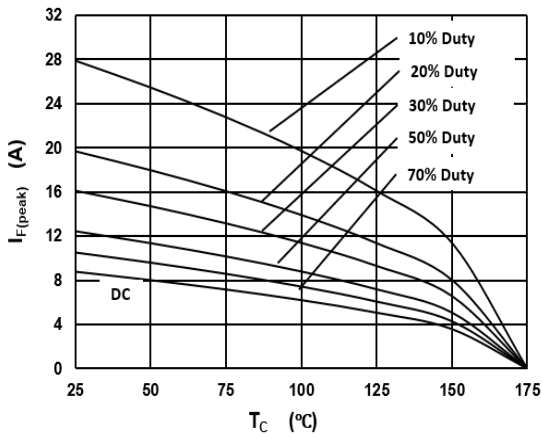


Fig 4: Power Derating

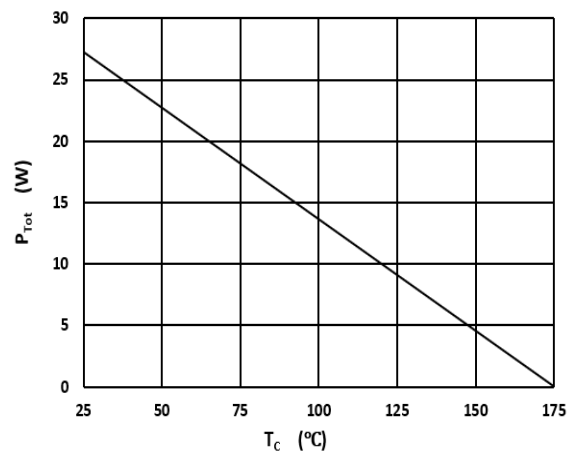


Fig 5: Capacitance vs. Reverse Voltage

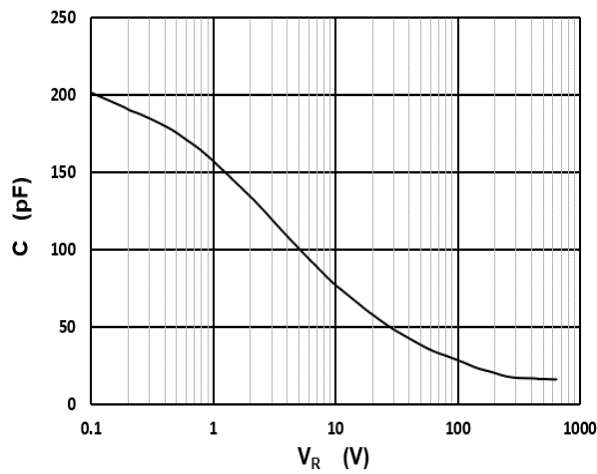


Fig 6: Reverse Charge vs. Reverse Voltage

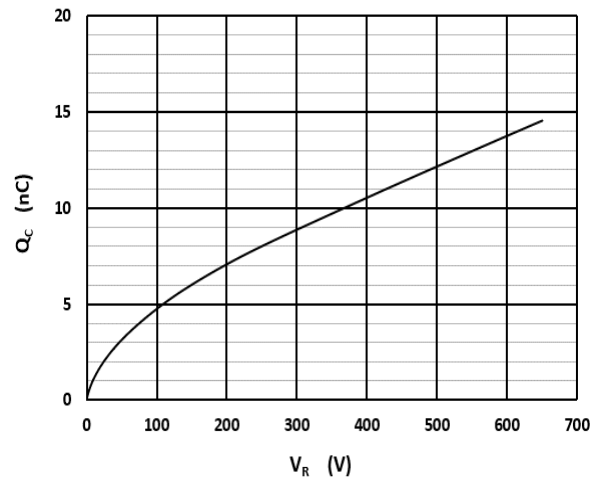


Fig 7: Typical Capacitance Stored Energy

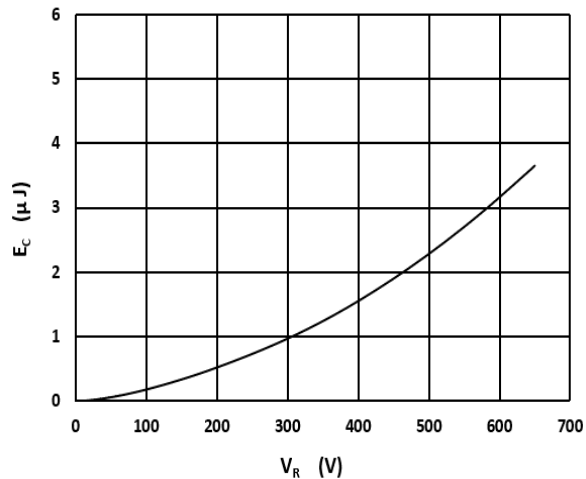
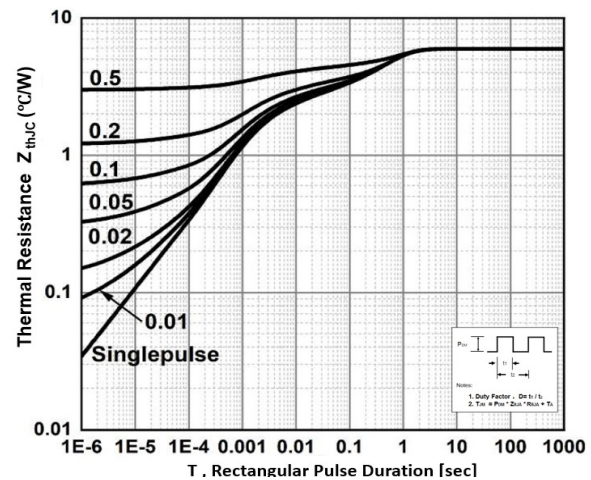
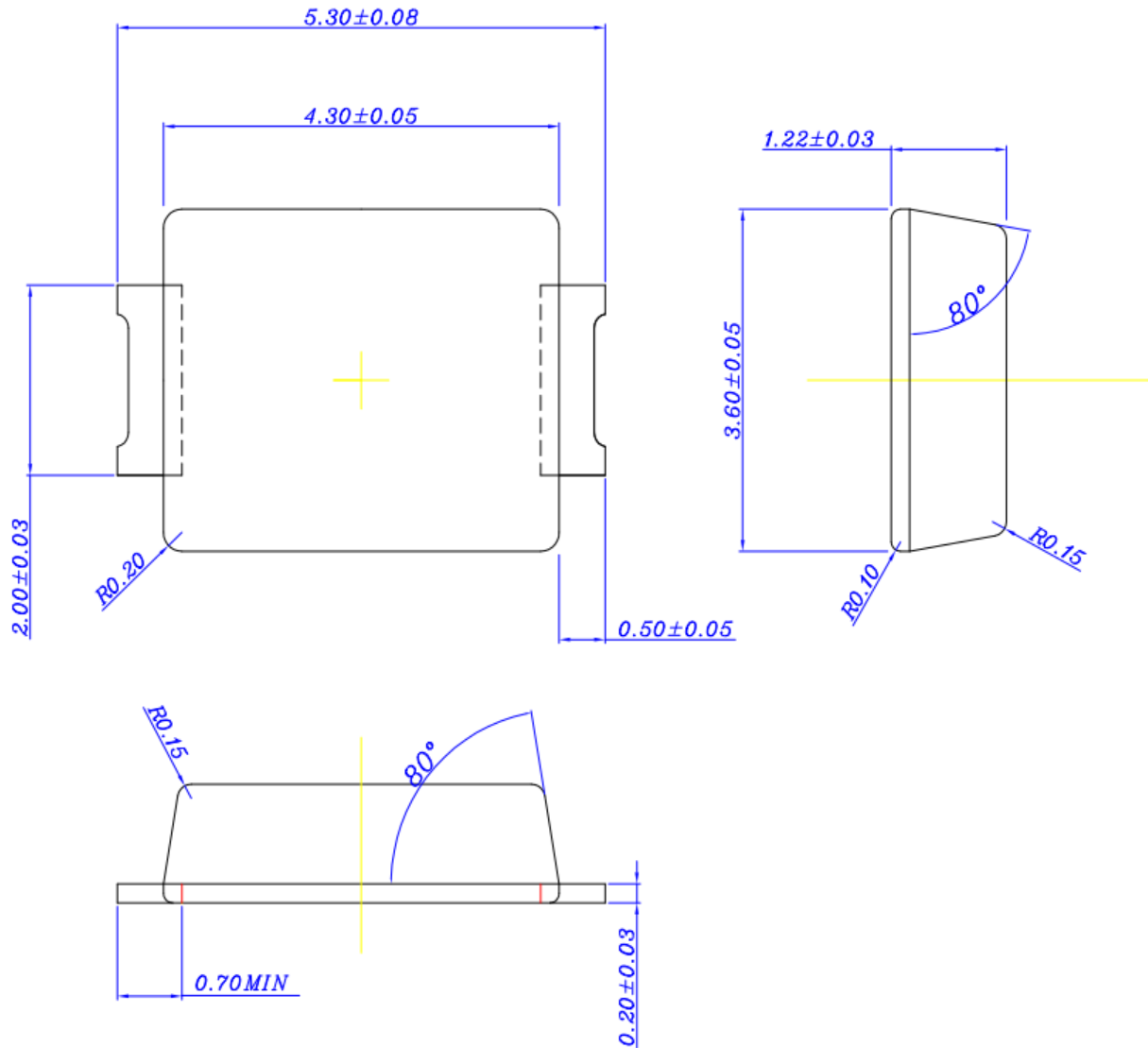


Fig 8: Transient Thermal Impandance





## Package Information SMBF





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